

# John Joyce

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4238682/publications.pdf>

Version: 2024-02-01

70  
papers

2,839  
citations

126708

33  
h-index

168136

53  
g-index

70  
all docs

70  
docs citations

70  
times ranked

1509  
citing authors



#	ARTICLE	IF	CITATIONS
19	Momentum-dependent effects in 4f photoemission spectra from strongly correlated CeBe <sub>13</sub> . Physical Review B, 1996, 53, 3317-3326.	1.1	59
20	Silicide formation at the Ti/Si(111) interface: Room-temperature reaction and Schottky-barrier formation. Physical Review B, 1987, 35, 6213-6221.	1.1	55
21	Temperature-invariant valence-band 4f photoemission features in the heavy-fermion compound YbAl <sub>3</sub> . Physical Review B, 1993, 48, 9497-9507.	1.1	54
22	Controlling Oxidation States in Uranium Oxides through Epitaxial Stabilization. Advanced Materials, 2007, 19, 3559-3563.	11.1	53
23	Modeling a heterogeneous metal/semiconductor interface: Ce on Si(111). Physical Review B, 1984, 30, 7370-7373.	1.1	49
24	Growth morphology and electronic structure of the Bi/GaAs(110) interface. Physical Review B, 1989, 40, 10412-10419.	1.1	44
25	Critical development stages for the reactive Cr-GaAs(110) interface. Physical Review B, 1985, 31, 5348-5354.	1.1	43
26	Strongly correlated electron systems: Photoemission and the single-impurity model. Physical Review B, 1997, 56, R7041-R7044.	1.1	42
27	Reactions at a rare-earth GaAs interface: Ce/GaAs(110). Physical Review B, 1985, 31, 5290-5296.	1.1	41
28	Adatom aggregation, reaction, and chemical trapping at the Sm/GaAs(110) interface. Physical Review B, 1985, 32, 962-968.	1.1	40
29	Core-level binding-energy shifts, thermodynamic predictions, and morphologies for metal-Si and metal-Ge interfaces. Physical Review B, 1987, 36, 4761-4768.	1.1	39
30	Disruption, segregation, and passivation for Pd and noble-metal overlayers on YBa <sub>2</sub> Cu <sub>3</sub> O <sub>6.9</sub> . Physical Review B, 1988, 38, 232-239.	1.1	39
31	Photoemission spectra of CeAl <sub>3</sub> , CeBe <sub>13</sub> , CeSi <sub>2</sub> , and CeCu <sub>2</sub> Si <sub>2</sub> : Weights and widths of the 4f emission features. Physical Review B, 1993, 47, 15460-15471.	1.1	36
32	Thermal work function shifts for polycrystalline metal surfaces. Surface Science, 2001, 478, 72-82.	0.8	36
33	Photoemission study of the development of the Ti/GaAs(110) interface. Physical Review B, 1986, 33, 2191-2197.	1.1	33
34	Asymmetries in atomic intermixing at Au/Ge and Ge/Au interfaces. Physical Review B, 1986, 34, 5118-5124.	1.1	30
35	Joyce and Arko reply. Physical Review Letters, 1993, 70, 1181-1182.	2.9	30
36	Direct Observation of Itinerant Magnetism in the 5f-Electron System UTe. Physical Review Letters, 2004, 93, 267205.	2.9	29

#	ARTICLE	IF	CITATIONS
37	Photoemission and the lack of a Kondo scale. Physical Review Letters, 1994, 72, 1774-1774.	2.9	28
38	Cluster formation and atomic intermixing at the reactive V/Ge(111) interface. Physical Review B, 1985, 32, 5149-5155.	1.1	26
39	Bulk electronic structure of YbInCu <sub>4</sub> from photoemission: a unique test of the single impurity model. Physical Review B, 2000, 62, 16492-16499.	1.1	23
40	4f photoemission from Ce clusters and disordered reaction products at Ce/Si and Ce/GaAs interfaces. Physical Review B, 1985, 31, 8291-8294.	1.1	21
41	Observation of a kink in the dispersion of f-electrons. Europhysics Letters, 2008, 84, 37003.	0.7	21
42	The 5f band structure of antiferromagnetic USb <sub>2</sub> from angle-resolved photoemission spectroscopy: Application to heavy fermions. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1997, 75, 603-610.	0.6	20
43	Chemical bonding in ordered Ce overlayers on Si(111). Physical Review B, 1987, 36, 1075-1079.	1.1	19
44	Modeling homogeneous and heterogeneous metal/semiconductor interface reactions with photoemission and angle-resolved auger spectroscopy. Surface Science, 1986, 168, 309-322.	0.8	18
45	A comparison of hybrid density functional theory with photoemission of surface oxides of $\delta$ -plutonium. Surface Science, 2006, 600, 1637-1640.	0.8	17
46	Synchrotron-radiation photoemission studies of interface formation between metals and superconductors: Al and In on YBa <sub>2</sub> Cu <sub>3</sub> O <sub>6.9</sub> . Physical Review B, 1988, 37, 3741-3744.	1.1	15
47	Photoemission in YbCu <sub>2</sub> Si <sub>2</sub> : problems with the Kondo impurity model. Journal of Magnetism and Magnetic Materials, 1992, 108, 215-216.	1.0	15
48	A tunable bench top light source for photoelectron spectroscopy: first results for alpha and delta Pu. Journal of Alloys and Compounds, 1999, 286, 14-19.	2.8	15
49	Preparation of Epitaxial Uranium Dicarbide Thin Films by Polymer-Assisted Deposition. Chemistry of Materials, 2013, 25, 4373-4377.	3.2	15
50	Crystal fields, linewidths and temperature dependence in the photoelectron spectra of heavy fermion Ce and Yb compounds. Solid State Communications, 1992, 83, 551-554.	0.9	14
51	Intrinsic Photoemission Spectra for YbB <sub>12</sub> . Physical Review Letters, 1997, 78, 1831-1831.	2.9	13
52	Electronic structure of single crystal UPd <sub>3</sub> , UGe <sub>2</sub> , and USb <sub>2</sub> from hard X-ray and angle-resolved photoelectron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2011, 184, 517-524.	0.8	13
53	Photoemission and the electronic properties of heavy fermions: limitations of the Kondo model. Physica B: Condensed Matter, 1995, 205, 365-370.	1.3	12
54	Comment on "Evidence of a Kondo scale from the temperature dependence of inverse photoemission spectroscopy of CePd <sub>3</sub> ". Physical Review Letters, 1992, 69, 3418-3418.	2.9	11

#	ARTICLE	IF	CITATIONS
55	Comparative study of the formation of Cr/Ge and Ge/Cr thin-film interfaces. <i>Physical Review B</i> , 1986, 33, 8039-8047.	1.1	9
56	Photoemission and electronic structure studies of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> . <i>Journal of Physics and Chemistry of Solids</i> , 1991, 52, 1437-1445.	1.9	9
57	Electronic structure of layered uranium compounds from photoemission spectroscopy. <i>Surface Science</i> , 2006, 600, 1632-1636.	0.8	9
58	CeSi <sub>2</sub> Photoemission Spectra at 5 meV Resolution. <i>Physical Review Letters</i> , 1998, 81, 1348-1348.	2.9	8
59	Chemical trapping and modification of the Au/GaAs(110) interface using Sm interlayers. <i>Physical Review B</i> , 1987, 36, 1605-1611.	1.1	7
60	Electronic structure studies of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> (6.2% $\tilde{A}$ — $\tilde{A}$ % 6.9) using angle-resolved photoemission. <i>Surface Science Reports</i> , 1993, 19, 121-142.	3.8	7
61	Valence-band photoemission and Auger-line-shape study of Au <sub>x</sub> Pd <sub>1-x</sub> . <i>Physical Review B</i> , 1994, 49, 16149-16155.	1.1	7
62	The electronic structure of La <sub>0.66</sub> Ca <sub>0.33</sub> MnO <sub>3</sub> and La <sub>1.2</sub> Sr <sub>1.8</sub> Mn <sub>2</sub> O <sub>7</sub> studied by angle resolved photoemission. <i>Journal of Applied Physics</i> , 2000, 88, 786-789.	1.1	7
63	He discharge lamp for photoemission experiments with radioactive materials. <i>Review of Scientific Instruments</i> , 2002, 73, 3750-3753.	0.6	6
64	Notes on the Dual Nature of 5f Electrons. <i>Journal of the Physical Society of Japan</i> , 2006, 75, 39-40.	0.7	6
65	Surface energy calculation $\hat{\epsilon}$ metals with 1 and 2 delocalized electrons per atom. <i>Chemical Physics</i> , 2002, 278, 111-117.	0.9	5
66	Inconsistencies with the single-impurity Anderson model in photoelectron spectra of cerium heavy fermion compounds. <i>Journal of Alloys and Compounds</i> , 1992, 181, 161-169.	2.8	3
67	Photoemission and x-ray studies of metal hydrides and hydride formation at metal/hydride interfaces. <i>Solid State Communications</i> , 1985, 55, 1089-1091.	0.9	1
68	Soft-x-ray photoemission study of Cr-Ge intermixing on crystalline and amorphous Ge surfaces. <i>Physical Review B</i> , 1986, 34, 4010-4016.	1.1	1
69	Localized and Itinerant States in Pu Materials. <i>Materials Research Society Symposia Proceedings</i> , 2005, 893, 1.	0.1	1
70	Band-bending model for the ideal Bi/InP(110) interface. <i>Physical Review B</i> , 1992, 46, 12818-12821.	1.1	0